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PATENT ABSTRACTS OF JAPAN

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(30) Priority:	(71) Applicant: TOSHIBA CORP
(43) Date of application publication: 06.10.86	(72) Inventor: KATSURA TOSHIHIKO ABE MASAYASU TAKAOKI KIYOSHI AOYAMA MASA HARU
(84) Designated contracting states:	(74) Representative:

**(54) REACTIVE ION
ETCHING APPRATUS**

(57) Abstract:

PURPOSE: To enable the wafer surface to be etched by a method wherein a material to reduce the etching species of reactive gas in the ratio almost the

CONSTITUTION: The faciang of an electrode 6 and an insulating sheet 10 are made larger than the outside diameter of a semiconductor 8 which a correcting ring 20 is provided between a step difference 12 due to the facing and the semi conductor wafer 8. Any material Abel to reduce etching species of reactive gas in the ratio subject to the difference between the etched materials but at least almost the same as that of any etched materials is applicable to the correcting ring 20. In such a constitution, there is a material to reduce the etching element in the peripheral part of semiconductor wafer as well as on the

semiconductor wafer therefore the part subject to uneven concentration of etching species (a) can be shifted to outside making the concentration of etching even on the semiconductor wafer 8. Resultantly, the semiconductor wafer 8 can be etched evenly.

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